

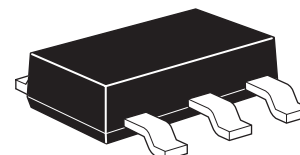
ZXMP7A17G

70V P-channel enhancement mode MOSFET

Summary

$V_{DSS}=70V : R_{DS(on)}=0.16\Omega$

$I_D=3.7A$

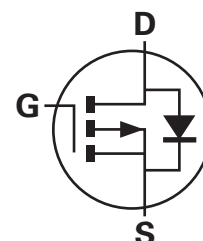


Description

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage power management applications.

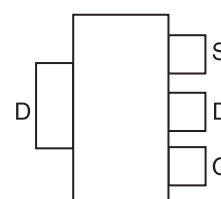
Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT223 package



Applications

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control
- Class D audio output stages



Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP7A17GTA	7	12	1,000
ZXMP7A17GTC	13	12	4,000

Device marking

ZXMP
7A17

ZXMP7A17G

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{DSS}	-70	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current @ $V_{GS}=10V$; $T_A=25^\circ C$ ^(b) @ $V_{GS}=10V$; $T_A=25^\circ C$ ^(b) @ $V_{GS}=10V$; $T_A=25^\circ C$ ^(a)	I_D	-3.7 -2.9 -2.6	A
Pulsed drain current ^(c)	I_{DM}	-9.6	A
Continuous source current (body diode) ^(b)	I_S	-4.8	A
Pulsed source current (body diode) ^(c)	I_{SM}	-9.6	A
Power dissipation at $T_A = 25^\circ C$ ^(a) Linear derating factor	P_D	2 16	W mW/ $^\circ C$
Power dissipation at $T_A = 25^\circ C$ ^(b) Linear derating factor	P_D	3.9 31	W mW/ $^\circ C$
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ C$

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	62.5	$^\circ C/W$
Junction to ambient ^(b)	$R_{\theta JA}$	32	$^\circ C/W$

NOTES:

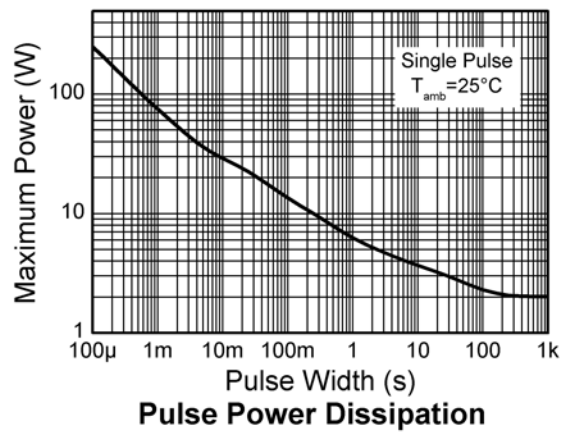
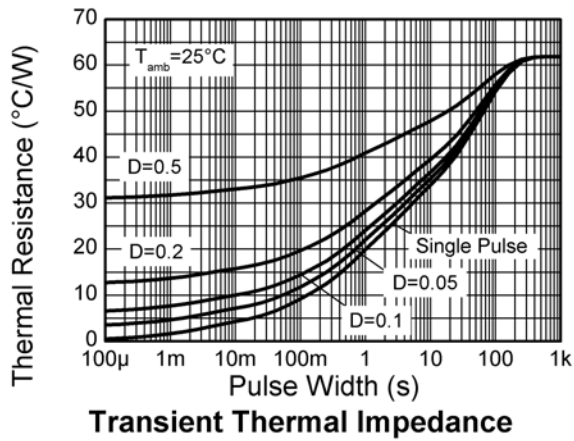
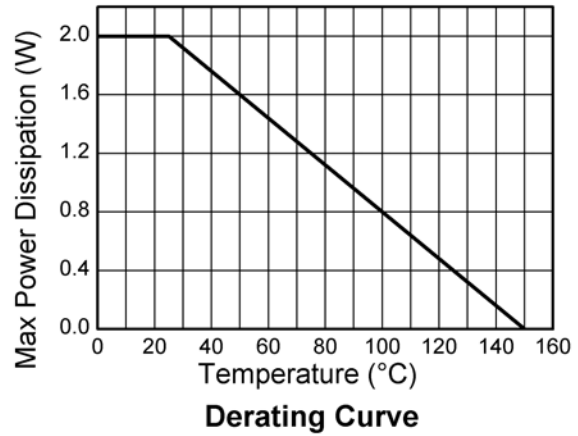
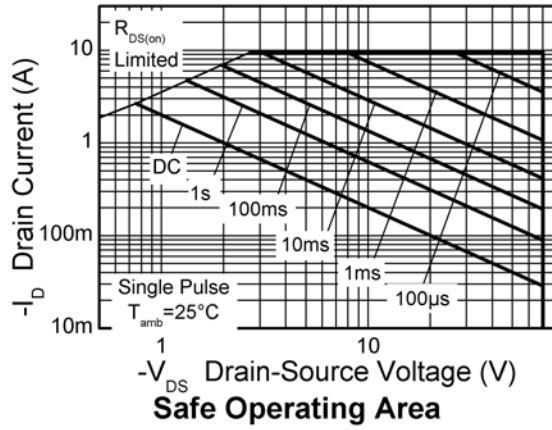
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ sec.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D=0.05$ pulse width=10 μs - pulse width limited by maximum junction temperature.

ZXMP7A17G

Characteristics



ZXMP7A17G

ELECTRICAL CHARACTERISTICS (at Tamb = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-source breakdown voltage	V _{(BR)DSS}	-70			V	I _D = -250μA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}			-1	μA	V _{DS} = -70V, V _{GS} =0V
Gate-body leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-source threshold voltage	V _{GS(th)}	-1.0			V	I _D = -250μA, V _{DS} =V _{GS}
Static drain-source on-state resistance ^(*)	R _{DS(on)}			0.16	Ω	V _{GS} = -10V, I _D = -2.1A
				0.25	Ω	V _{GS} = -4.5V, I _D = -1.7A
Forward transconductance ^{(*)(‡)}	g _{fs}		4.4		S	V _{DS} = -15V, I _D = -2.1A
Dynamic ^(‡)						
Input capacitance	C _{iss}		635		pF	V _{DS} = -40V, V _{GS} =0V f=1MHz
Output capacitance	C _{oss}		52		pF	
Reverse transfer capacitance	C _{rss}		42.5		pF	
Switching ^{(†)(‡)}						
Turn-on-delay time	t _{d(on)}		2.5		ns	V _{DD} = -35V, I _D = -1A R _G ≐6.0Ω, V _{GS} = -10V
Rise time	t _r		3.4		ns	
Turn-off delay time	t _{d(off)}		27.9		ns	
Fall time	t _f		8		ns	
Total gate charge	Q _g		9.6		nC	V _{DS} = -35V, V _{GS} = -5V I _D = -2.1A
Total gate charge	Q _g		18		nC	V _{DS} = -35V, V _{GS} = -10V I _D = -2.1A
Gate-source charge	Q _{gs}		1.77		nC	
Gate drain charge	Q _{gd}		3.66		nC	
Source-drain diode						
Diode forward voltage ^(*)	V _{SD}		-0.85	-0.95	V	T _j =25°C, I _S = -2.0A, V _{GS} =0V
Reverse recovery time ^(‡)	t _{rr}		29.8		ns	T _j =25°C, I _S = -2.1A, di/dt=100A/μs
Reverse recovery charge ^(‡)	Q _{rr}		38.5		nC	

NOTES:

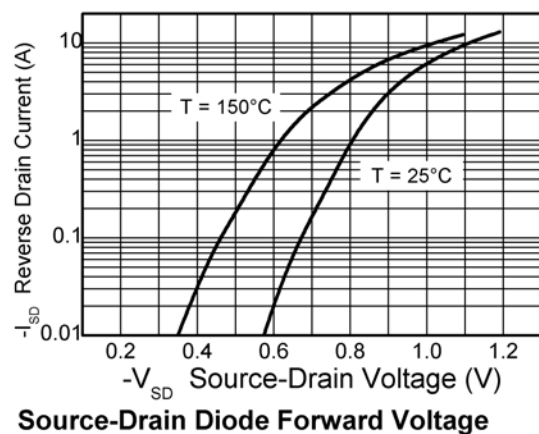
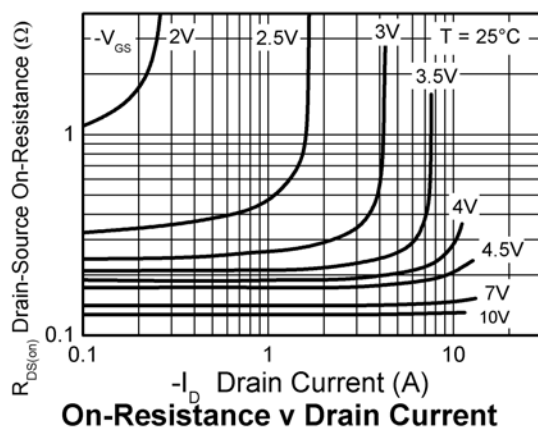
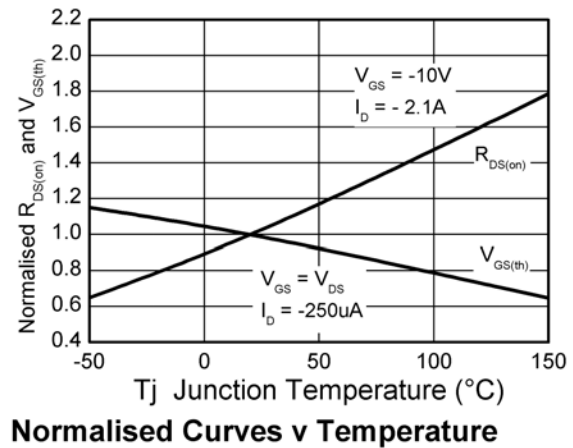
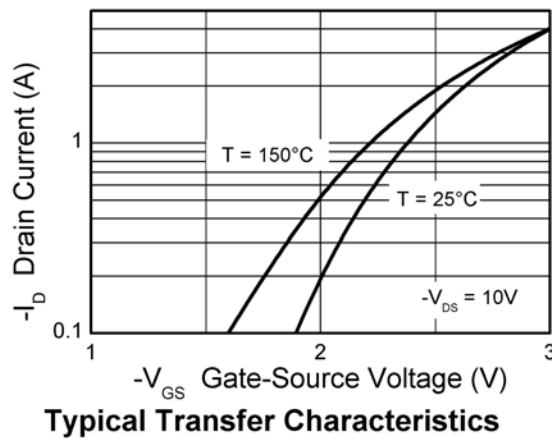
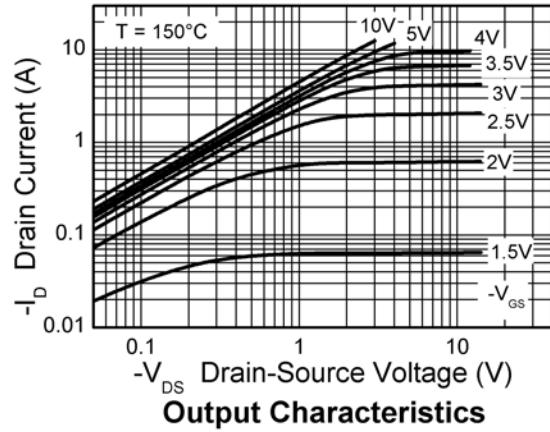
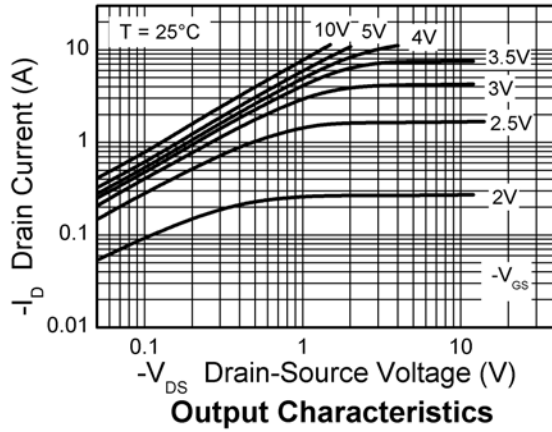
(*) Measured under pulsed conditions. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.

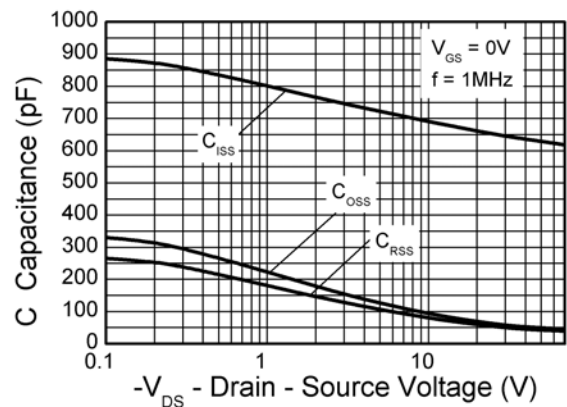
ZXMP7A17G

Typical characteristics

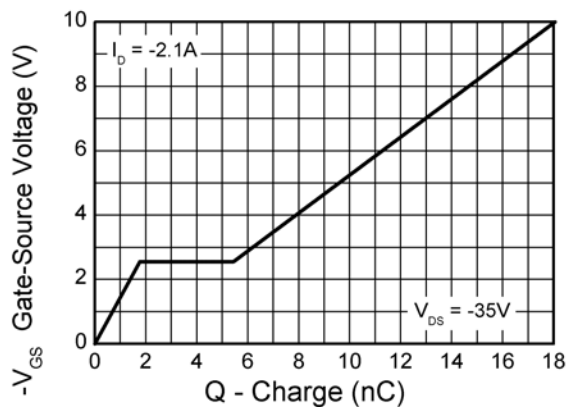


ZXMP7A17G

Typical characteristics



Capacitance v Drain-Source Voltage



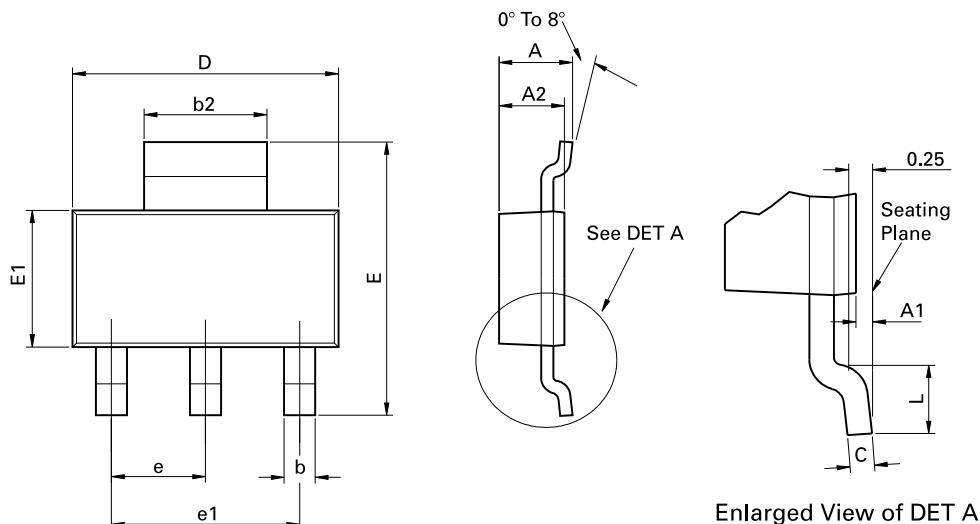
Gate-Source Voltage v Gate Charge

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ZXMP7A17G

Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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